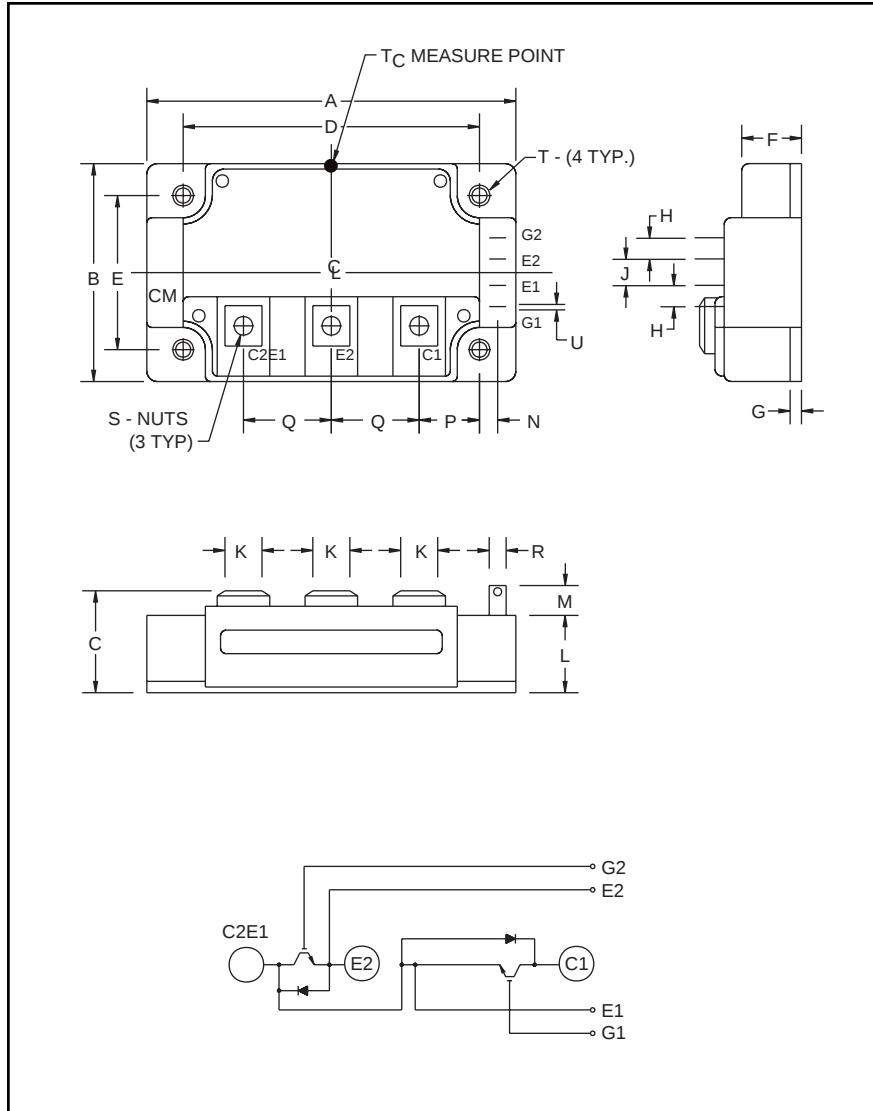


Trench Gate Design Dual IGBTMOD™ 400 Amperes/250 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.25	108.0
B	2.44	62.0
C	1.14 +0.04/-0.02	29.0 +1.0/-0.5
D	3.66±0.01	93.0±0.25
E	1.88±0.01	48.0±0.25
F	0.67	17.0
G	0.16	4.0
H	0.24	6.0
J	0.59	15.0
K	0.55	14.0

Dimensions	Inches	Millimeters
L	0.87	22.0
M	0.33	8.5
N	0.10	2.5
P	0.85	21.5
Q	0.98	25.0
R	0.11	2.8
S	M6	M6
T	0.26 Dia.	6.5 Dia.
U	0.002	0.05



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies
- ☐ Laser Power Supplies

Ordering Information:

Example: Select the complete module number you desire from the table - i.e. CM400DU-5F is a 250V (V_{CES}), 400 Ampere Dual IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	400	5

CM400DU-5F

Trench Gate Design Dual IGBTMOD™

400 Amperes/250 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	CM400DU-5F	Units
Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	250	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current ($T_c = 25^\circ\text{C}$)	I_c	400	Amperes
Peak Collector Current ($T_j \leq 150^\circ\text{C}$)	I_{CM}	800*	Amperes
Emitter Current** ($T_c = 25^\circ\text{C}$)	I_E	400	Amperes
Peak Emitter Current**	I_{EM}	800*	Amperes
Maximum Collector Dissipation ($T_c = 25^\circ\text{C}$)	P_c	890	Watts
Mounting Torque, M6 Main Terminal	–	40	in-lb
Mounting Torque, M6 Mounting	–	40	in-lb
Weight	–	400	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	Volts

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(\text{max})}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

Static Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{\text{CE}} = V_{\text{CES}}, V_{\text{GE}} = 0\text{V}$	–	–	1.0	mA
Gate Leakage Current	I_{GES}	$V_{\text{GE}} = V_{\text{GES}}, V_{\text{CE}} = 0\text{V}$	–	–	0.5	μA
Gate-Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$I_c = 40\text{mA}, V_{\text{CE}} = 10\text{V}$	3.0	4.0	5.0	Volts
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	$I_c = 400\text{A}, V_{\text{GE}} = 10\text{V}, T_j = 25^\circ\text{C}$	–	1.2	1.7	Volts
		$I_c = 400\text{A}, V_{\text{GE}} = 10\text{V}, T_j = 125^\circ\text{C}$	–	1.1	–	Volts
Total Gate Charge	Q_G	$V_{\text{CC}} = 100\text{V}, I_c = 400\text{A}, V_{\text{GE}} = 10\text{V}$	–	1500	–	nC
Emitter-Collector Voltage*	V_{EC}	$I_E = 400\text{A}, V_{\text{GE}} = 0\text{V}$	–	–	2.0	Volts

* Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(\text{max})}$ rating.

Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

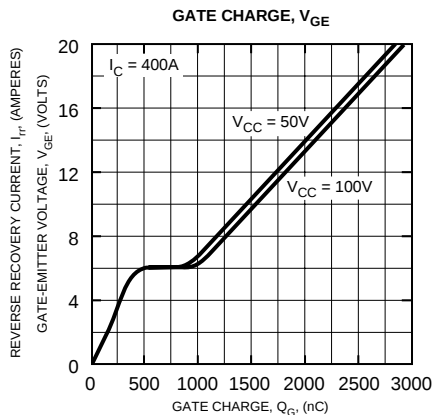
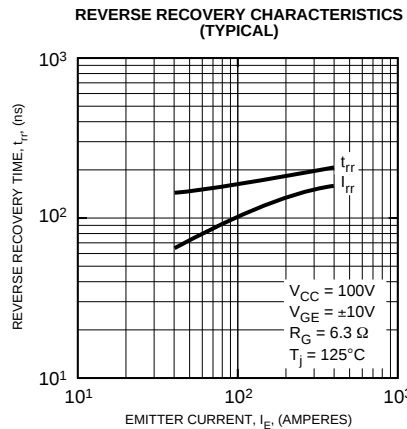
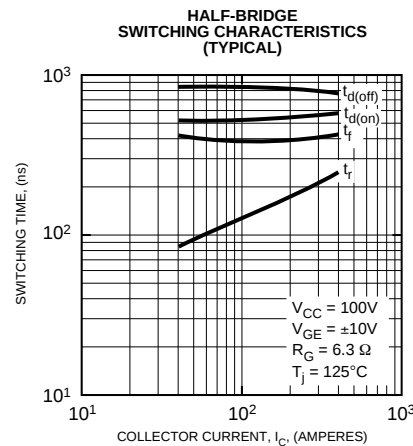
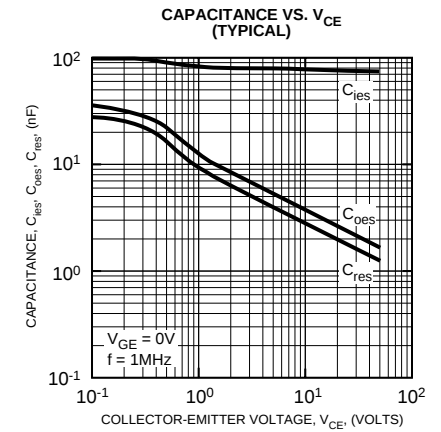
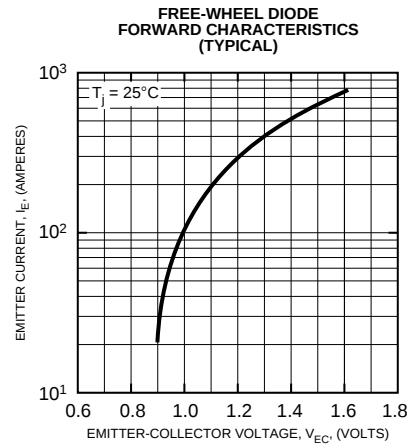
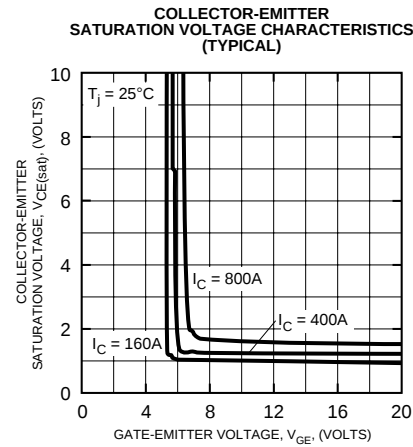
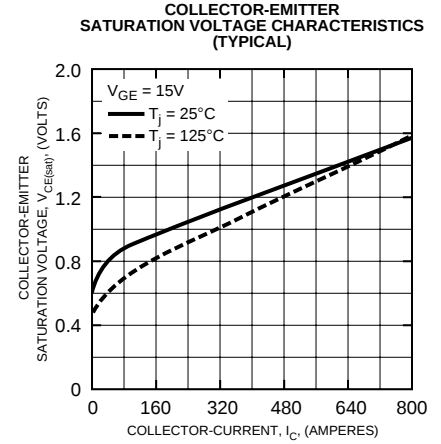
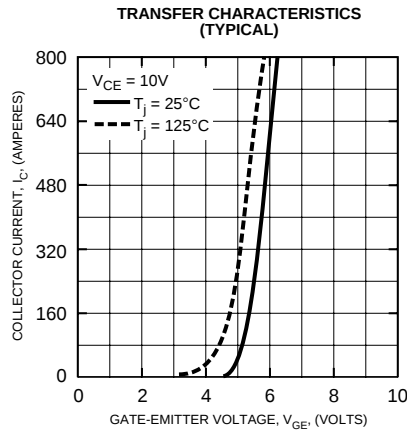
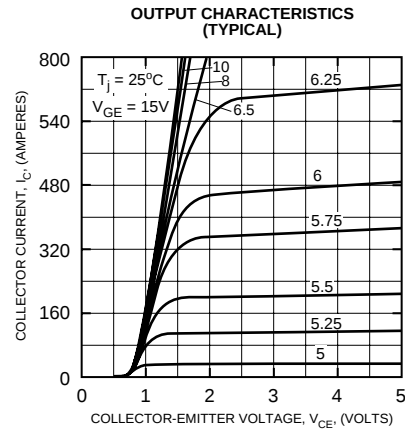
Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0V	–	–	110	nf
Output Capacitance		C _{oes}		–	–	7.0	nf
Reverse Transfer Capacitance		C _{res}		–	–	3.8	nf
Resistive Load	Turn-on Delay Time	t _{d(on)}	V _{CC} = 100V, I _C = 400A,	–	–	850	ns
	Rise Time	t _r	V _{GE1} = V _{GE2} = 10V,	–	–	400	ns
Switch Times	Turn-off Delay Time	t _{d(off)}	R _G = 6.3Ω, Resistive	–	–	1100	ns
	Fall Time	t _f	Load Switching Operation	–	–	500	ns
Diode Reverse Recovery Time		t _{rr}	I _E = 400A	–	–	300	ns
Diode Reverse Recovery Charge		Q _{rr}	I _E = 400A	–	16.0	–	μC

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)Q}}$	Per IGBT 1/2 Module	–	–	0.14	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)D}}$	Per FWDi 1/2 Module	–	–	0.24	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\text{th(j-c')Q}}$	Per IGBT 1/2 Module*	–	–	0.08	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{\text{th(c-f)}}$	Per Module, Thermal Grease Applied	–	0.04	–	$^\circ\text{C/W}$

* T_c measured point is just under chip.

CM400DU-5F
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